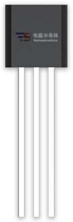
2SB1322A TRANSISTOR (PNP)



FEATURES

- Allowing Supply with The Radial Taping

ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
2SB1322A	TO-92	Bul	1000pcs/Bag
2SB1322A-TA	TO-92	Tape	2000pcs/Box

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-1	A
P_D	Collector Power Dissipation	625	mW
$R_{\theta JA}$	Thermal Resistance ˇrom Junction ˇo Ambient	200	℃ /W
T_J,T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	℃

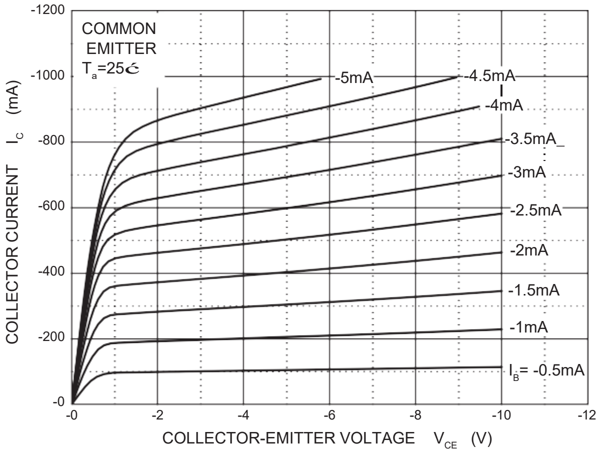
T_a=25℃ unless otherwise specified

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C= -0.01mA,I_E=0	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-2mA,I_B=0	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-0.01mA,I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-20V,I_E=0			-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-5V,I_C=0			-0.1	μA
DC current gain	$h_{FE(1)}$	V_{CE}=-10V, I_C=-0.5A	85		340	
	$h_{FE(2)}$	V_{CE}=-5V, I_C=-1A	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-0.5A,I_B=-0.05A			-0.4	V
Base-emitter saturation voltage	$V_{BE\ (sat)}$	I_C=-0.5A,I_B=-0.05A			-1.2	V
Collector output capacitance	C_{ob}	V_{CB}=-10V,I_E=0, f=1MHz			30	pF
Transition frequency	f_T	VCE=-10V,Ic= -0.05A, f=200MHz		200		MHz

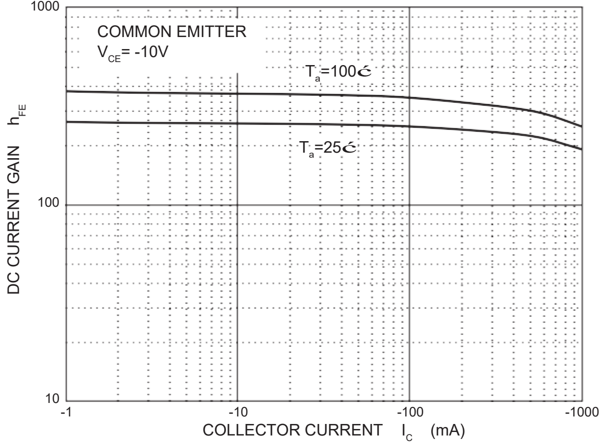
CLASSIFICATION OF $h_{FE(1)}$

RANK	Q	R	S
RANGE	85-170	120-240	170-340

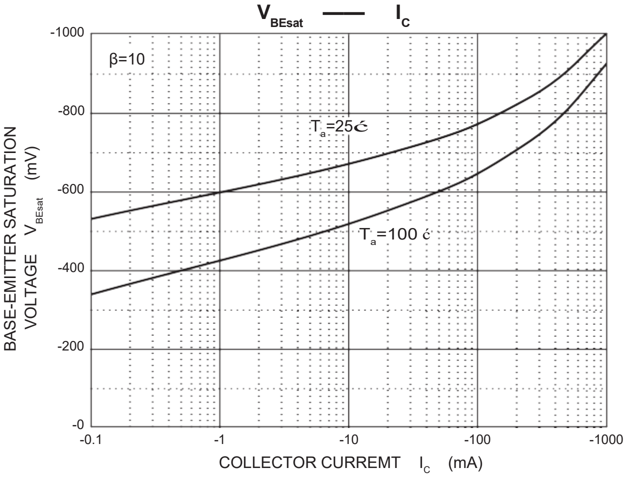
Static Characteristic



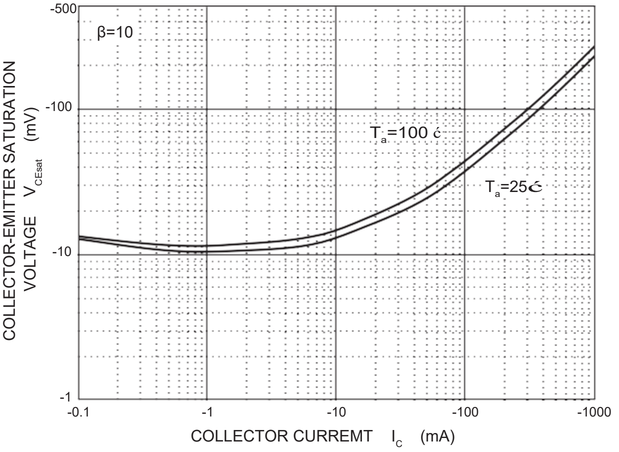
h_{FE} — I_C



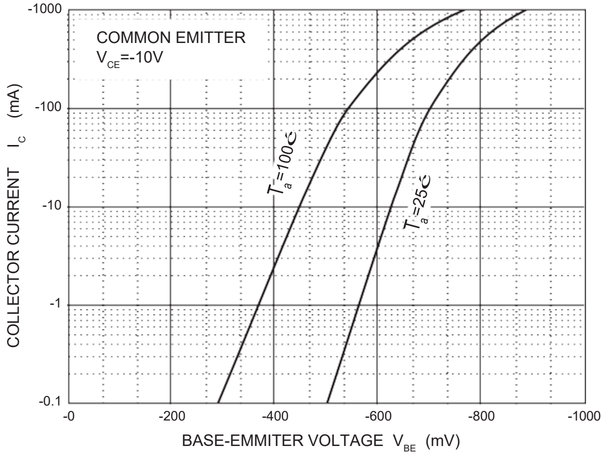
V_{BEsat} — I_C



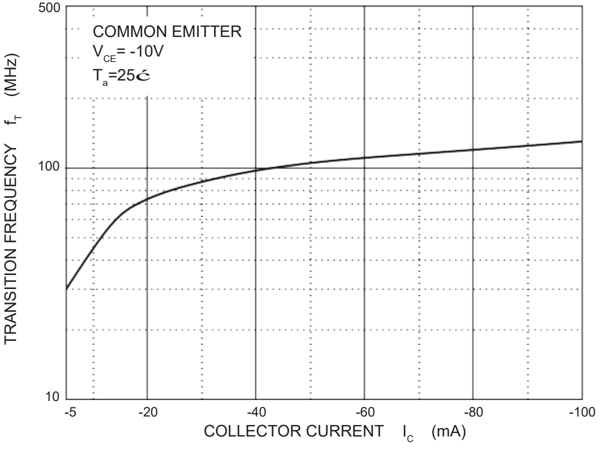
V_{CEsat} — I_C



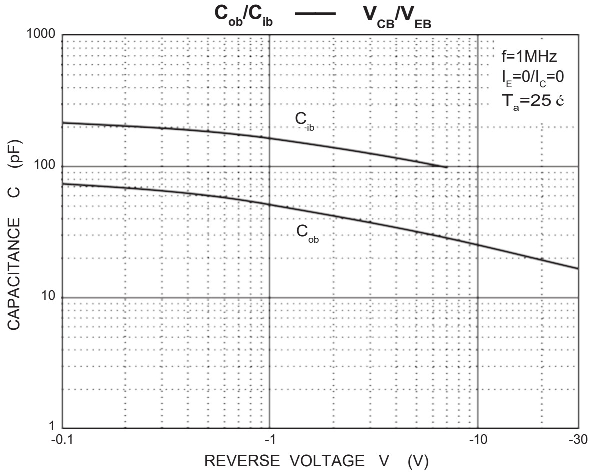
I_C — V_{BE}



f_T — I_C



C_{ob}/C_{ib} — V_{CB}/V_{EB}



P_C — T_a